

**GENERAL  
INSTRUMENT**

## NON-ZERO-CROSSING TRIACS

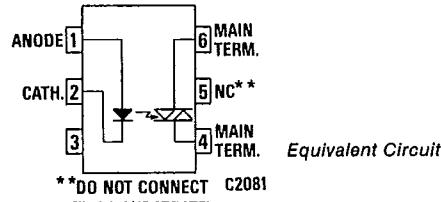
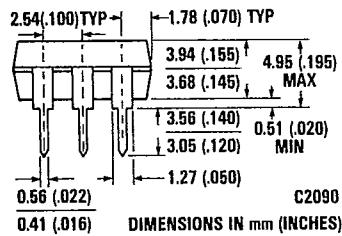
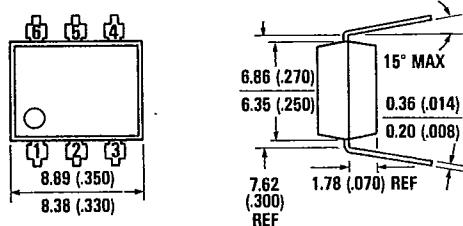
Optocouplers

**30 mA MCP3009\***

**NON-ZERO-CROSSING 15 mA MCP3010**

**10 mA MCP3011**

### PACKAGE DIMENSIONS



### DESCRIPTION

The MCP3009, MCP3010 and MCP3011 are optically isolated triac driver devices. These devices contain a GaAs infrared emitting diode and a light activated silicon bilateral switch, which functions like a triac. This series is designed for interfacing between electronic controls and power triacs to control resistive and inductive loads for 120 VAC operations.

### FEATURES

- Low input current required (typically 5mA – MCP3011)
- Minimum commutating dv/dt is specified at 0.1V/ $\mu$ sec
- Pin for pin replacement for the MOC3009, 3010 and 3011 devices
- High isolation voltage – minimum 7500 VAC peak
- Underwriters Laboratory (UL) recognized – File E50151

### APPLICATIONS

- Triac driver
- Industrial controls
- Traffic lights
- Vending machines
- Motor control
- Solid state relay

\*Not Recommended  
For New Designs

### ABSOLUTE MAXIMUM RATINGS

#### TOTAL PACKAGE

Storage temperature .....	-55°C to 150°C
Operating temperature .....	-40°C to 100°C
Lead temperature (Soldering 10 sec .....	260°C
Total package power dissipation @ 25°C (LED plus detector) .....	330 mW
Derate linearly from 25°C .....	4.0 mW/°C
Withstand test voltage .....	7500 VAC Peak (50-60 Hz)

#### INPUT DIODE

Forward DC current .....	60 mA
Reverse voltage .....	3 V
Peak forward current (1 $\mu$ s pulse, 300 pps) .....	3.0 A
Power dissipation 25°C ambient .....	100 mW
Derate linearly from 25°C .....	1.33 mW/°C

#### OUTPUT DRIVER

Off-state output terminal voltage .....	250 volts
On-state RMS current TA = 25°C .....	100 mA
(Full cycle, 50 to 60 Hz) TA = 70°C .....	50 mA
Peak nonrepetitive surge current .....	1.2 A
(PW = 10 ms, DC = 10%)	
Total power dissipation @ TA = 25°C .....	300 mW
Derate above 25°C .....	4.0 mW/°C

**MCP3009 MCP3010 MCP3011****ELECTRO-OPTICAL CHARACTERISTICS (25°C Temperature Unless Otherwise Specified)**

	TRANSFER CHARACTERISTICS						
	CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
DC	LED Trigger Current (Current Required to latch output)	I <sub>FT</sub>	—	15.0	30	mA	Main terminal voltage = 3.0 V
	MCP3009 MCP3010 MCP3011		—	10.0	15		
dv/dt RATING	Holding Current	I <sub>H</sub>	—	200	—	μA	Either direction
	Critical Rate of Rise of Off-State Voltage	dv/dt	—	10.0	—	V/μs	Static dv/dt (see Figure 5)
ISOLATION	Critical Rate of Rise of Commutating Voltage	dv/dt	0.1	0.2	—	V/μs	Commutating dv/dt I <sub>LOAD</sub> = 15 mA (see Figure 5)
	Isolation Voltage	V <sub>Iso</sub>	5300			V <sub>ACRMS</sub>	Relative humidity < 50%, I <sub>I-O</sub> < 10 μA, 5 seconds
		V <sub>Iso</sub>	7500			V <sub>ACPEAK</sub>	Relative humidity < 50%, I <sub>I-O</sub> < 10 μA, 5 seconds
	Isolation resistance	R <sub>Iso</sub>	10 <sup>11</sup>			ohms	V <sub>I-O</sub> = 500 VDC
	Isolation capacitance	C <sub>Iso</sub>		0.5		pF	f = 1 MHz

	INDIVIDUAL COMPONENT CHARACTERISTICS						
	CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
INPUT DIODE	Forward voltage	V <sub>F</sub>		1.3	1.50	V	I <sub>F</sub> = 30 mA
	Forward voltage temp. coefficient			-1.8		mV/°C	
	Reverse breakdown voltage	BV <sub>R</sub>	3.0	25		V	I <sub>R</sub> = 10 μA
	Junction capacitance	C <sub>J</sub>		50		pF	V <sub>F</sub> = 0 V, f = 1 MHz
				65		pF	V <sub>F</sub> = 1 V, f = 1 MHz
OUTPUT DETECTOR	Reverse leakage current	I <sub>R</sub>	.35	10		μA	V <sub>R</sub> = 3.0 V
	Peak Blocking Current, Either Direction	I <sub>DRM</sub>	—	10	100	nA	V <sub>DRM</sub> = 250 V, Note 1
	Peak On-State Voltage, Either Direction	V <sub>TM</sub>	—	2.0	3.0	Volts	I <sub>TM</sub> = 100 mA Peak
	Note 1. Test voltage must be applied within dv/dt rating.						

**TYPICAL ELECTRICAL CHARACTERISTIC CURVES**  
(25°C Free Air Temperature Unless Otherwise Specified)

Optocouplers

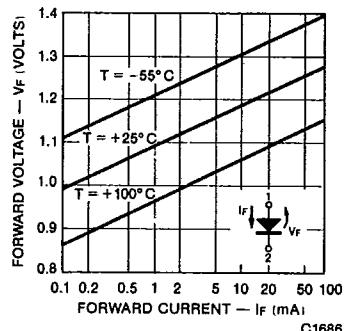


Fig. 1. Forward Voltage Drop vs. Forward Current

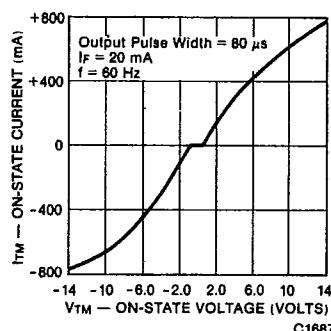


Fig. 2. On-State Characteristics

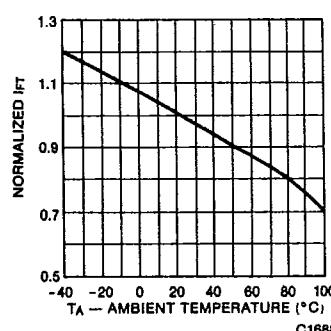
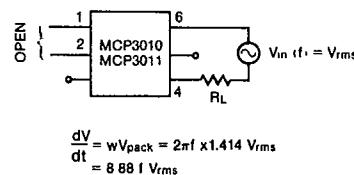
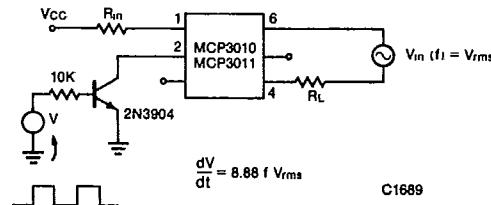


Fig. 3. Trigger Current vs. Temperature

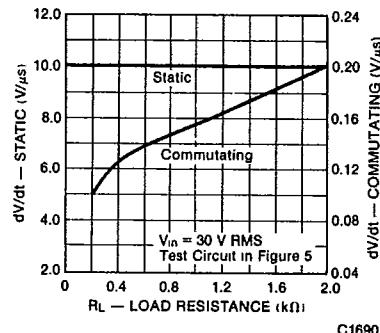
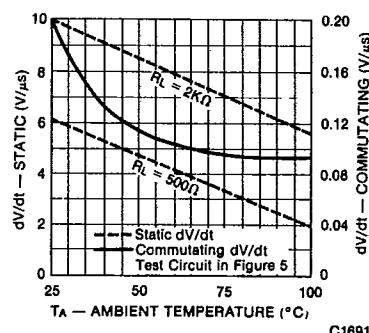
STATIC —  $dV/dt$  TEST CIRCUIT

$$\frac{dV}{dt} = \omega V_{\text{pack}} = 2\pi f \times 1.414 V_{\text{rms}} \\ = 8.88 f V_{\text{rms}}$$

COMMUTATING —  $dV/dt$  TEST CIRCUIT

$$\frac{dV}{dt} = 8.88 f V_{\text{rms}}$$

C1689

Fig. 4.  $dV/dt$  Test CircuitsFig. 5.  $dV/dt$  vs. Load ResistanceFig. 6.  $dV/dt$  vs. Temperature

# MCP3009 MCP3010 MCP3011

## TYPICAL ELECTRICAL CHARACTERISTIC CURVES

(25°C Temperature Unless Otherwise Specified)

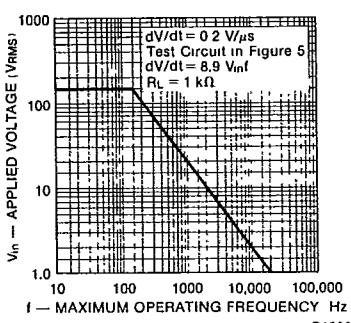


Fig. 7. Commutating  $dV/dt$   
vs Frequency

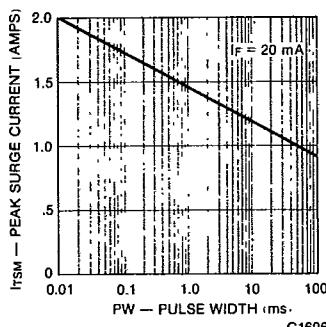


Fig. 8. Maximum Nonrepetitive  
Surge Current

## TYPICAL APPLICATION CIRCUITS

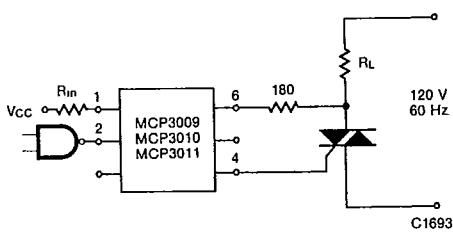


Fig. 9. Resistive Load

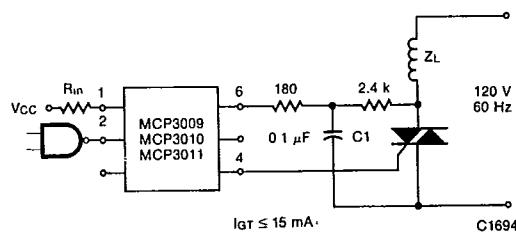


Fig. 10. Inductive Load With  
Sensitive Gate Triac

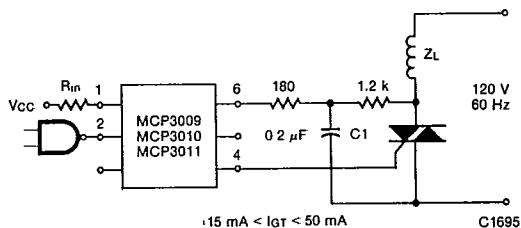


Fig. 11. Inductive Load With  
Non-Sensitive Gate Triac